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- 59. (new) A method of forming electrodes on first and second respective regions of a semiconductor structure, comprising:
- a. depositing metal on a surface of a first region of the semiconductor structure;
- b. forming a patterned mask over the metal on the surface of the first region, the mask having an opening so that a first portion is covered by the mask and a second portion aligned with the opening is left uncovered by the mask by applying a resist on the metal to form a resist layer, and lithographically patterning the resist layer to form the opening over the second region so that the remaining resist layer overlies the semiconductor structure in the first region;
- c. removing metal aligned with the opening in the second portion thereby defining a first electrode overlying and making electrical contact with the first region of the semiconductor structure;
- d. removing material of the semiconductor structure aligned with the opening in the second portion to expose a surface of the second region of the semiconductor structure by etching the semiconductor structure while the resist layer remains over the semiconductor structure in the first region; and
- e. forming a second electrode making electrical contact with the second region of the semiconductor structure
- 60. (new) The method of claim 59, wherein the step of depositing metal comprises depositing a first metal and subsequently depositing a second metal over the first metal.
- 61. (new) The method of claim 60, wherein the first metal comprises nickel and the second metal comprises gold, and further comprising annealing the structure so that the metal layers form a substantially transparent material.
- 62. (new) The method of claim 59, wherein the step of depositing comprises electron beam deposition.

Period added